

SK8403180L

Silicon N-channel MOS FET

For Load-switching / For DC-DC Converter

■ Features

- Low Drain-source On-state Resistance : $R_{DS(on)}$ typ = 6.7 m Ω (VGS = 4.5 V)
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : 18

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

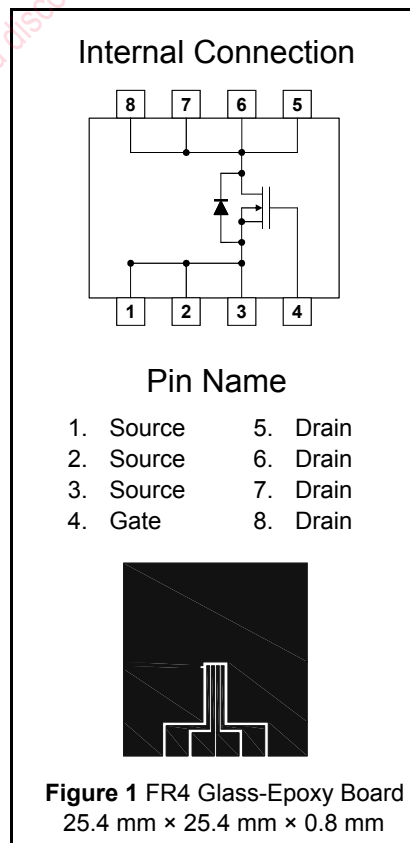
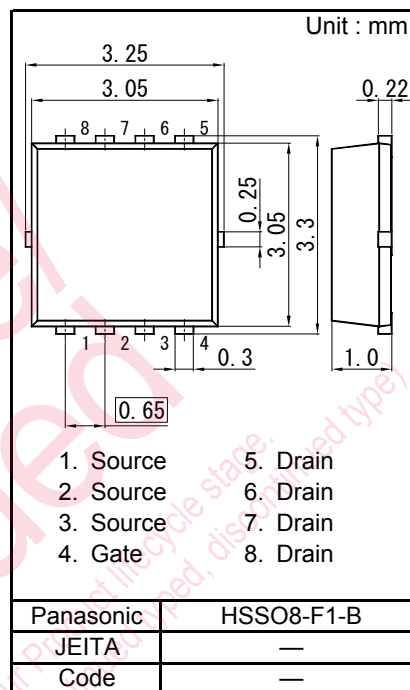
■ Absolute Maximum Ratings Ta = 25 °C

| Parameter | Symbol | Rating | Unit |
|--|--------------------|------------------------------------|------|
| Drain to Source Voltage | VDS | 30 | V |
| Gate to Source Voltage | VGS | ±20 | |
| Drain Current | ID | Ta = 25 °C, t = 10 s ^{*1} | 17 |
| | | Ta = 25 °C, DC ^{*1} | 12 |
| | | Tc = 25 °C | 39 |
| | | Pulsed, Tch < 150 °C ^{*2} | 51 |
| Total Power Dissipation | PD | Ta = 25 °C, DC ^{*1} | 2 |
| | | Tc = 25 °C | 19 |
| Thermal Resistance | Channel to Ambient | Rth(ch-a) | 62.5 |
| | Channel to Case | Rth(ch-c) | 6.6 |
| Channel Temperature | Tch | 150 | °C |
| Operating ambient temperature | Topr | -40 to +85 | |
| Storage Temperature Range | Tstg | -55 to +150 | |
| Avalanche Current (Single pulse) ^{*3} | IAR | 8.5 | A |
| Avalanche Energy (Single pulse) ^{*3} | EAR | 9 | mJ |

Note *1 Device mounted on a glass-epoxy board in Figure 1

*2 Pulse test: Ensure that the channel temperature does not exceed 150 °C

*3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25 °C (initial)



■ Electrical Characteristics Ta = 25 °C ± 3 °C

Static Characteristics

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|----------------------------------|----------|--------------------------|-----|-----|-----|------|
| Drain-source Breakdown Voltage | VDSS | ID = 1 mA, VGS = 0 V | 30 | | | V |
| Zero Gate Voltage Drain Current | IDSS | VDS = 30 V, VGS = 0 V | | | 10 | μA |
| Gate-source Leakage Current | IGSS | VGS = ±16 V, VDS = 0 V | | | ±10 | μA |
| Gate-source Threshold Voltage | Vth | ID = 1.45 mA, VDS = 10 V | 1.3 | | 3 | V |
| Drain-source On-state Resistance | RDS(on)1 | ID = 8.5 A, VGS = 10 V | | 5.1 | 7.1 | mΩ |
| | RDS(on)2 | ID = 8.5 A, VGS = 4.5 V | | 6.7 | 9.8 | |

Dynamic Characteristics

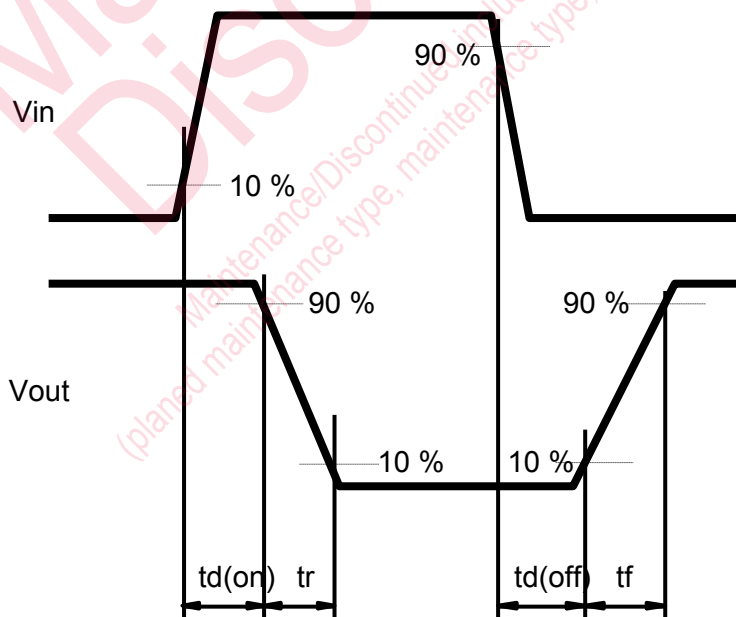
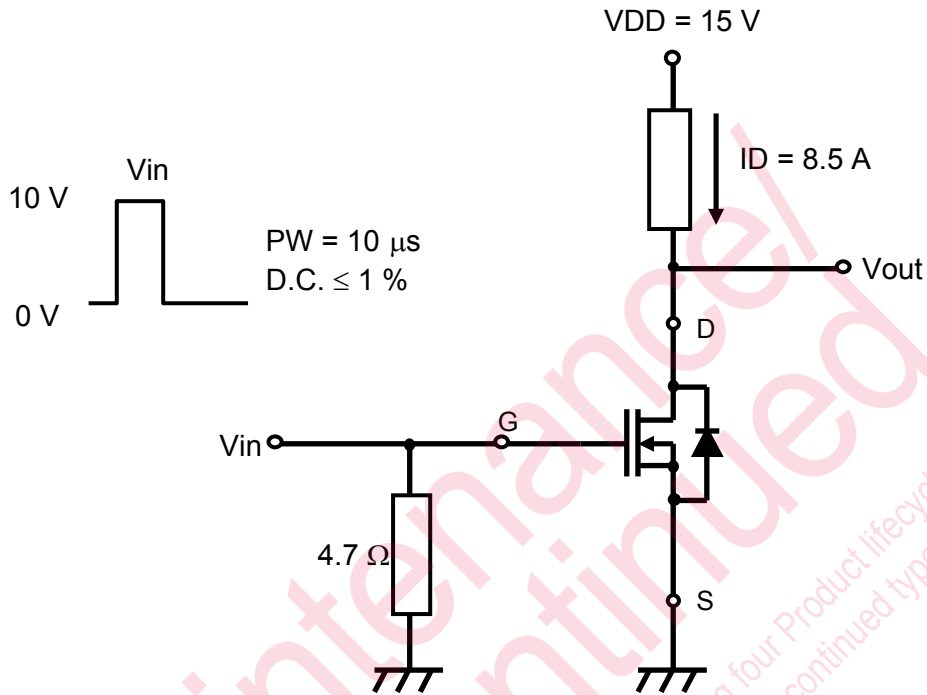
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|------------------------------|---------|--|-----|-------|-------|------|
| Input Capacitance | Ciss | VDS = 10 V, VGS = 0 V f = 1 MHz | | 1 200 | 1 680 | pF |
| Output Capacitance | Coss | | | 140 | 200 | |
| Reverse Transfer Capacitance | Crss | | | 100 | 160 | |
| Turn-on Delay Time*1 | td(on) | VDD = 15 V, VGS = 0 to 10 V | | 8 | | ns |
| Rise Time*1 | tr | ID = 8.5 A | | 6 | | |
| Turn-off Delay Time*1 | td(off) | VDD = 15 V, VGS = 10 to 0 V | | 39 | | ns |
| Fall Time*1 | tf | ID = 8.5 A | | 6 | | |
| Total Gate Charge | Qg | VDD = 15 V, VGS = 0 to 4.5 V ID = 8.5 A | | 10 | | nC |
| Gate to Source Charge | Qgs | | | 3 | | |
| Gate to Drain Charge | Qgd | | | 4 | | |
| Gate resistance | rg | f = 5 MHz | | 1.2 | 3 | Ω |

Body Diode Characteristic

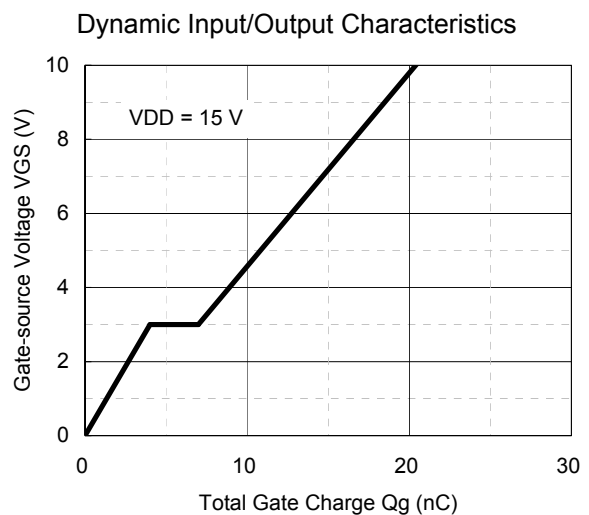
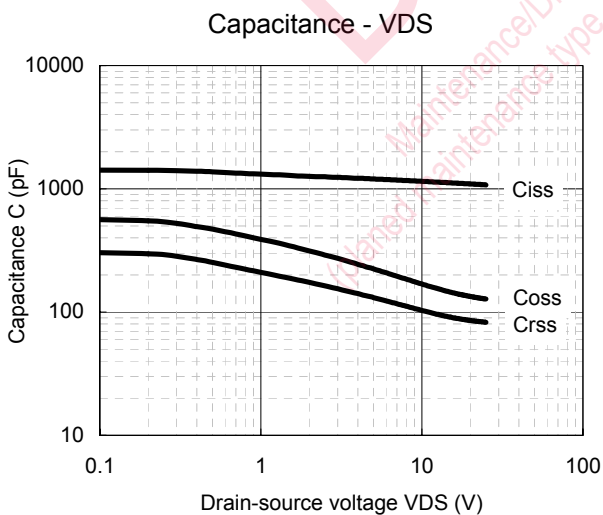
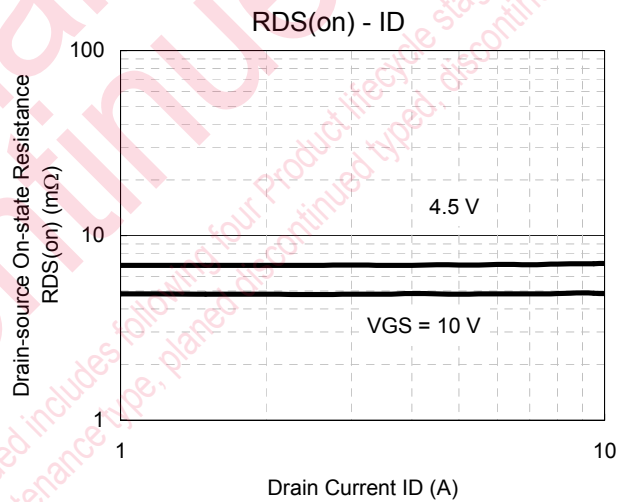
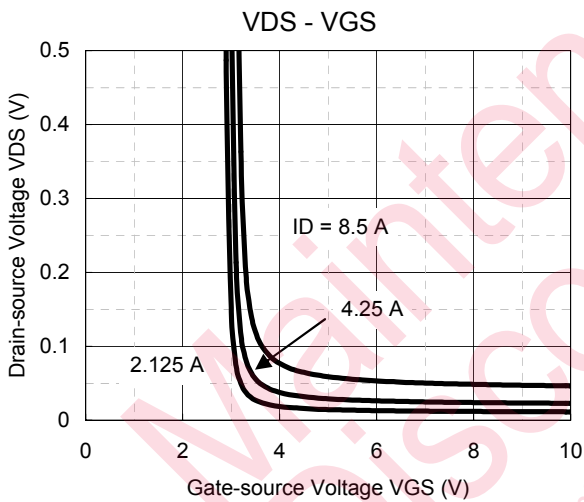
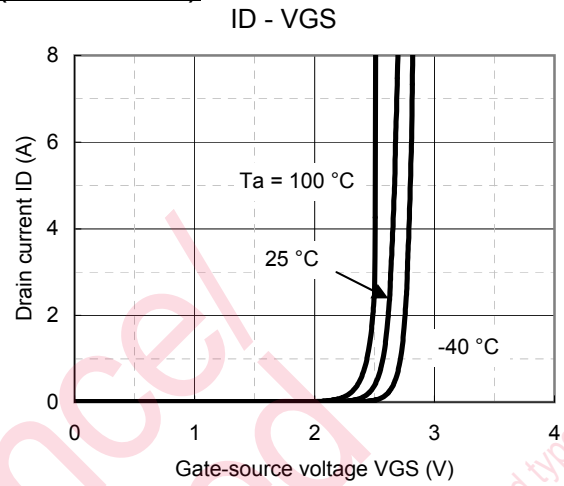
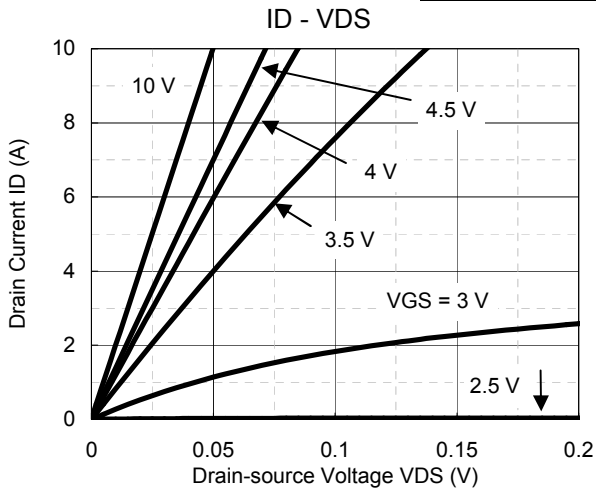
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|-----------------------|--------|-----------------------|-----|-----|-----|------|
| Diode Forward Voltage | VSD | IS = 8.5 A, VGS = 0 V | | 0.8 | 1.2 | V |

Note : 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.
2. *1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

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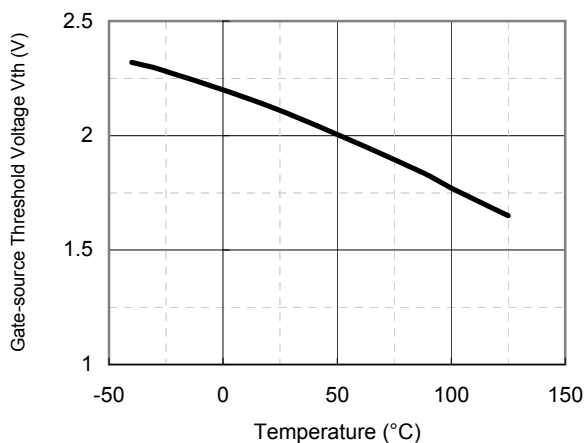


Technical Data (reference)

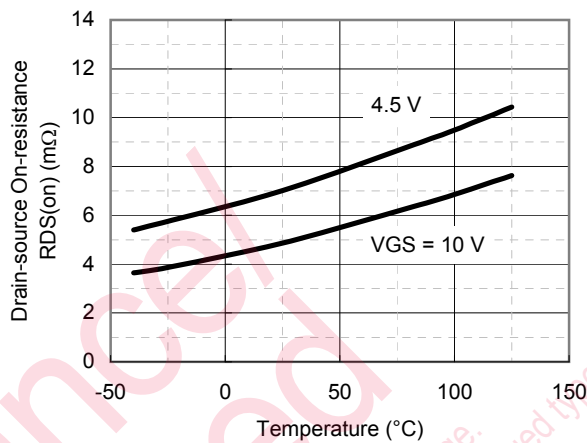


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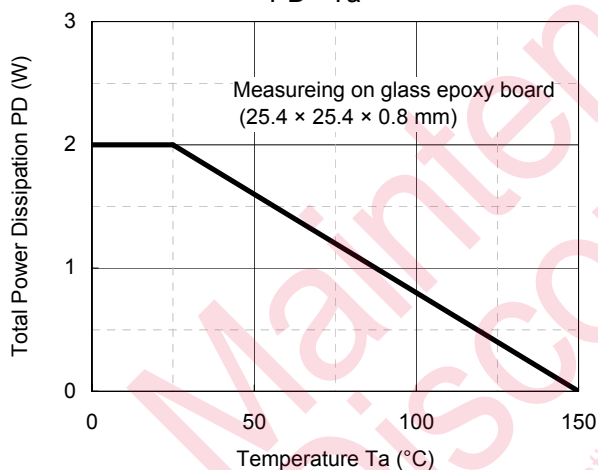
Vth - Ta



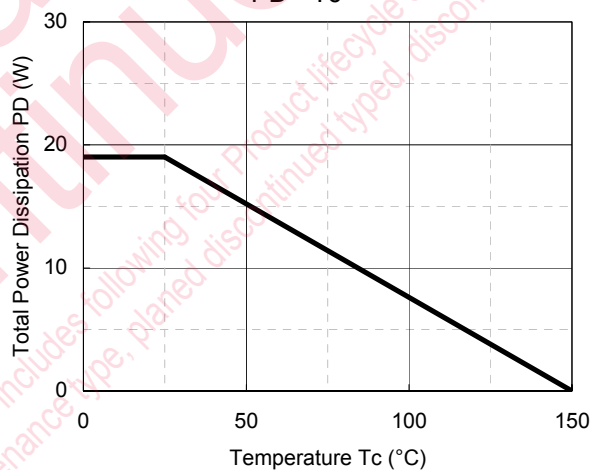
RDS(on) - Ta



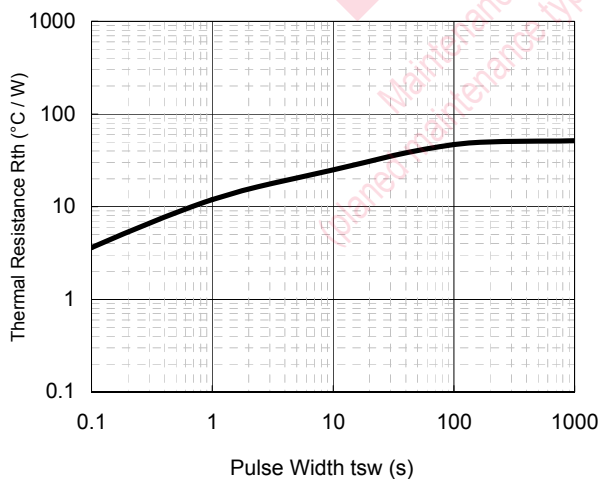
PD - Ta



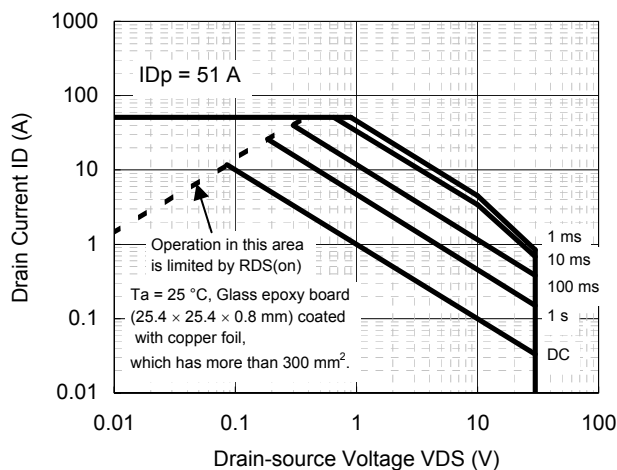
PD - Tc



Rth - tsw

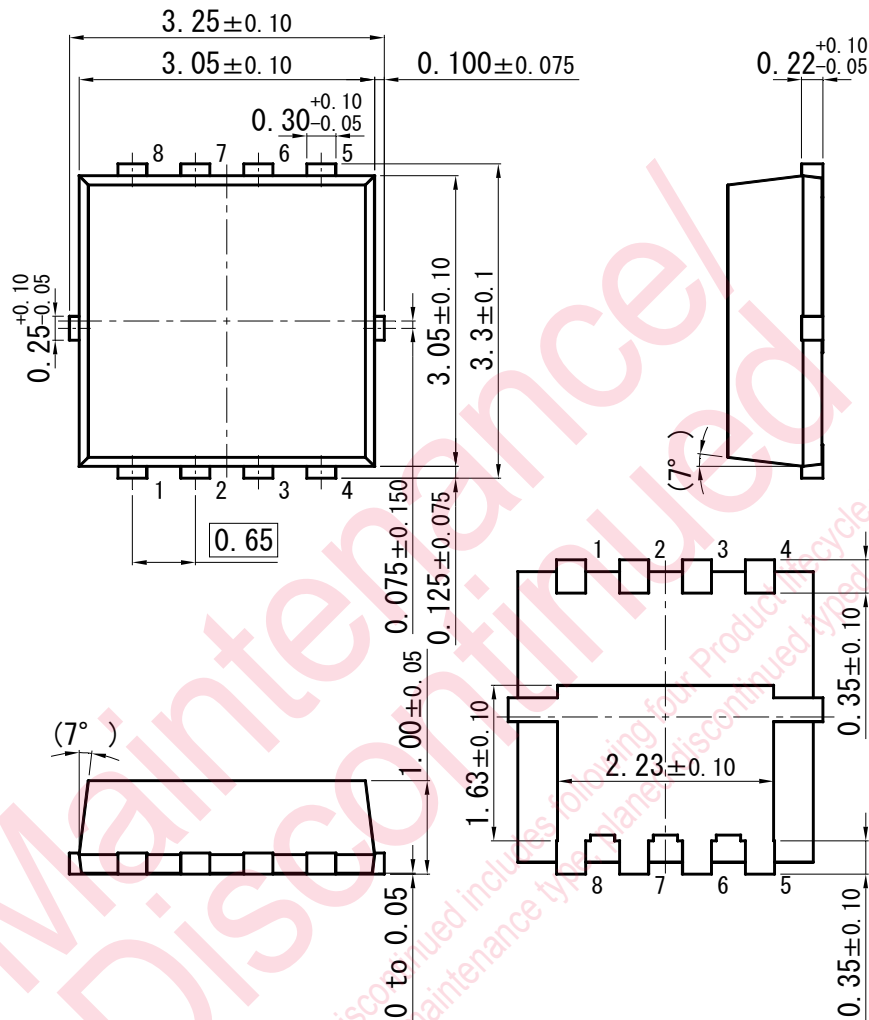


Safe Operating Area

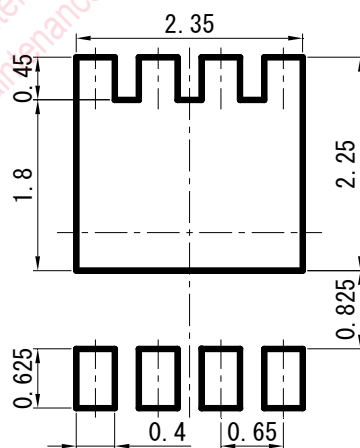


HSSO8-F1-B

Unit: mm



■ Land Pattern (Reference) (Unit : mm)



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